

10. (Amended) A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of Claim 1, thereby smoothening the semiconductor substrate.

REMARKS

Claims 1-7 and 9-10 are active in the present application. Claim 8 has been canceled. Claims 7 and 9-10 have been amended to remove multiple dependencies. Claim 7 has been amended to include further components of the polishing liquid composition. Amended Claim 7 is supported by the specification on page 5, lines 1-3. No new matter is added. An action on the merits and allowance of claims is solicited.

Respectfully submitted,

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Serial No:

Amendment Filed on:

1-10-2002

IN THE CLAIMS

7. (Amended) The polishing liquid composition according to [any one of claims 1 to 5] Claim 1, further comprising an oxidizing agent, an abrasive or a mixture thereof.

8. (Canceled).

9. (Amended) A process for polishing a semiconductor substrate, comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of [any one of claims 1 to 8] Claim 1, thereby smoothening the semiconductor substrate.

10. (Amended) A process for manufacturing a semiconductor substrate comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of [any one of claims 1 to 8] Claim 1, thereby smoothening the semiconductor substrate.